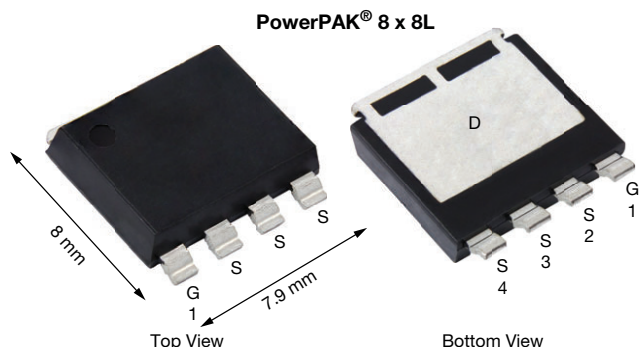


N-Channel 80 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY

V _{DS} (V)	80
R _{DS(on)} max. (Ω) at V _{GS} = 10 V	0.00155
R _{DS(on)} max. (Ω) at V _{GS} = 7.5 V	0.00180
Q _g typ. (nC)	140
I _D (A) ^a	288
Configuration	Single

ORDERING INFORMATION

Package	PowerPAK 8 x 8L
Lead (Pb)-free and halogen-free	SIJH800E-T1-GE3

ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V _{DS}	80	V
Gate-source voltage		V _{GS}	±20	
Continuous drain current (T _J = 150 °C)	T _C = 25 °C	I _D	299	A
	T _C = 70 °C		241	
	T _A = 25 °C		29 ^b	
	T _A = 70 °C		24 ^b	
Pulsed drain current (t = 100 μs)		I _{DM}	350	
Continuous source-drain diode current	T _C = 25 °C	I _S	303	
	T _A = 25 °C		3 ^b	
Single pulse avalanche current	L = 0.1 mH	I _{AS}	70	
Single pulse avalanche energy		E _{AS}	245	mJ
Maximum power dissipation	T _C = 25 °C	P _D	333	W
	T _C = 70 °C		233	
	T _A = 25 °C		3.3 ^b	
	T _A = 70 °C		2.3 ^b	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) ^c			260	

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient ^b	Steady state	R _{thJA}	36	45	°C/W
Maximum junction-to-case (drain)	Steady state	R _{thJC}	0.36	0.45	

Notes

a. $T_C = 25\text{ }^{\circ}\text{C}$

b. Surface mounted on 1" x 1" FR4 board

c. See solder profile (www.vishay.com/doc?73257). The PowerPAK 8 x 8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

d. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

FEATURES

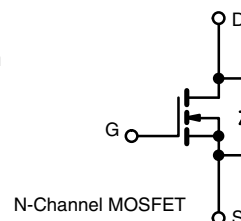
- TrenchFET® Gen IV power MOSFET
- Fully lead (Pb)-free device
- Optimized Q_g , Q_{gd} , and Q_{gd}/Q_{gs} ratio reduces switching related power loss
- 50 % smaller footprint than D²PAK (TO-263)
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc/99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Synchronous rectification
- OR-ing
- Motor drive control
- Battery management
- Power supply





SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	80	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	$I_D = 10\text{ mA}$	-	62	-	mV/ $^{\circ}\text{C}$
$V_{GS(th)}$ temperature coefficient	$\Delta V_{GS(th)}/T_J$	$I_D = 250\text{ }\mu\text{A}$	-	-11	-	
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2	-	4	V
Gate-source leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20$	-	-	100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 80\text{ V}$, $V_{GS} = 0\text{ V}$	-	-	1	μA
		$V_{DS} = 80\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 70\text{ }^{\circ}\text{C}$	-	-	15	
Drain-source on-state resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 20\text{ A}$	-	0.00122	0.00155	Ω
		$V_{GS} = 7.5\text{ V}$, $I_D = 20\text{ A}$	-	0.00131	0.00180	
Forward transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}$, $I_D = 50\text{ A}$	-	200	-	S
Dynamic ^b						
Input capacitance	C_{iss}	$V_{DS} = 40\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$	-	10 230	-	pF
Output capacitance	C_{oss}		-	1100	-	
Reverse transfer capacitance	C_{rss}		-	34	-	
Total gate charge	Q_g	$V_{DS} = 40\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 20\text{ A}$	-	140	210	nC
Gate-source charge	Q_{gs}	$V_{DS} = 40\text{ V}$, $V_{GS} = 7.5\text{ V}$, $I_D = 20\text{ A}$	-	106	160	
Gate-drain charge	Q_{gd}		-	46	-	
Gate resistance	R_g	$f = 1\text{ MHz}$	-	22	-	Ω
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 40\text{ V}$, $R_L = 10\text{ }\Omega$, $I_D \cong 4\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\text{ }\Omega$	0.2	1.1	2.2	ns
Rise time	t_r		-	20	40	
Turn-off delay time	$t_{d(off)}$		-	10	20	
Fall time	t_f		-	52	100	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 40\text{ V}$, $R_L = 10\text{ }\Omega$, $I_D \cong 4\text{ A}$, $V_{GEN} = 7.5\text{ V}$, $R_g = 1\text{ }\Omega$	-	15	30	
Rise time	t_r		-	25	50	
Turn-off delay time	$t_{d(off)}$		-	12	25	
Fall time	t_f		-	47	90	
			-	15	30	
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I_S	$T_C = 25\text{ }^{\circ}\text{C}$	-	-	303	A
Pulse diode forward current	I_{SM}		-	-	350	
Body diode voltage	V_{SD}	$I_S = 10\text{ A}$, $V_{GS} = 0\text{ V}$	-	0.7	1.1	V
Body diode reverse recovery time	t_{rr}	$I_F = 10\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25\text{ }^{\circ}\text{C}$	-	77	155	ns
Body diode reverse recovery charge	Q_{rr}		-	154	310	nC
Reverse recovery fall time	t_a		-	43	-	ns
Reverse recovery rise time	t_b		-	35	-	

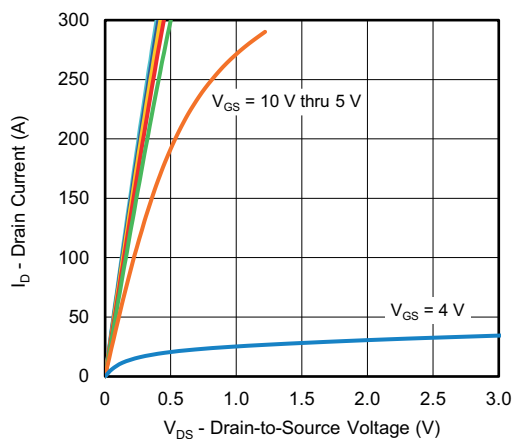
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing

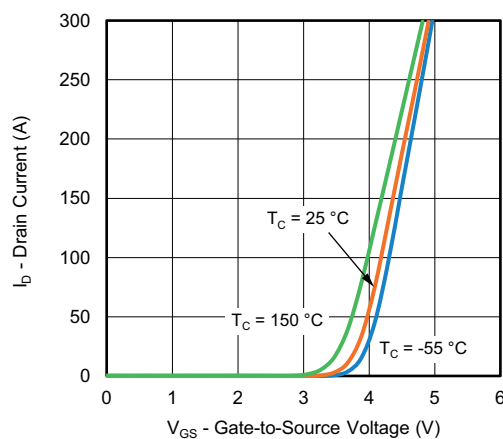
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



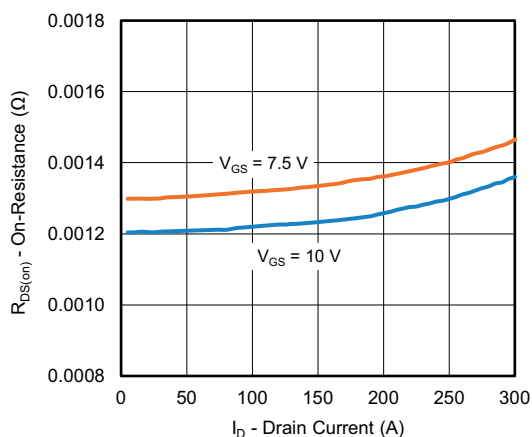
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



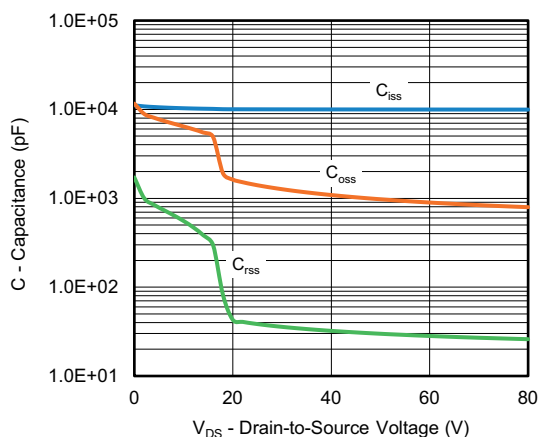
Output Characteristics



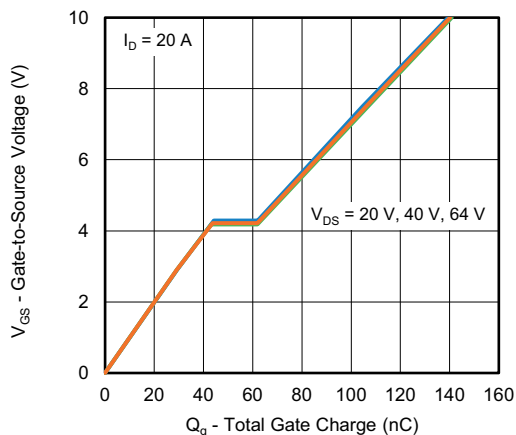
Transfer Characteristics



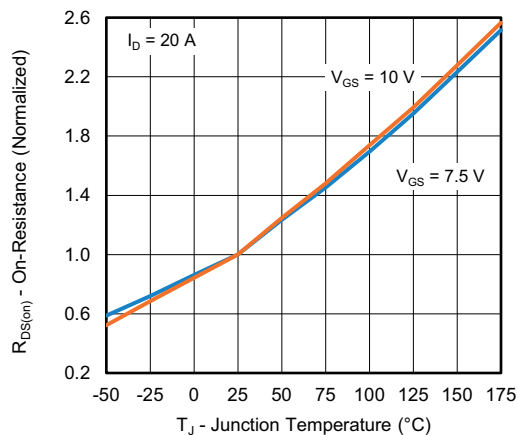
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



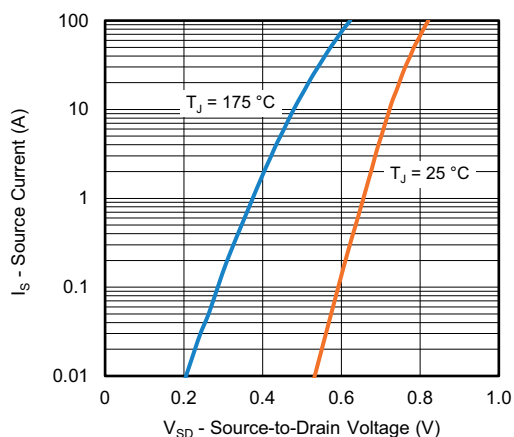
Gate Charge



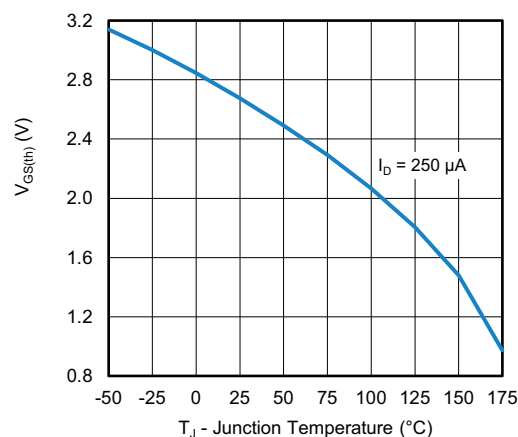
On-Resistance vs. Junction Temperature



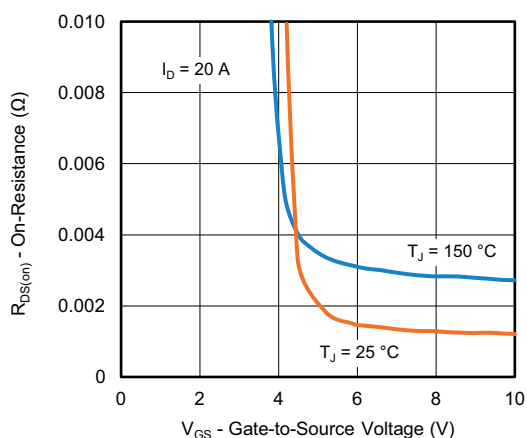
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



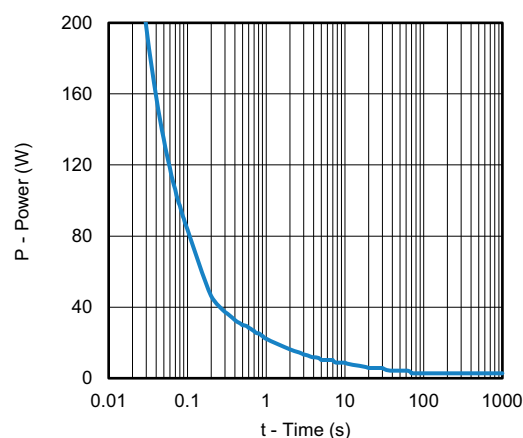
Source-Drain Diode Forward Voltage



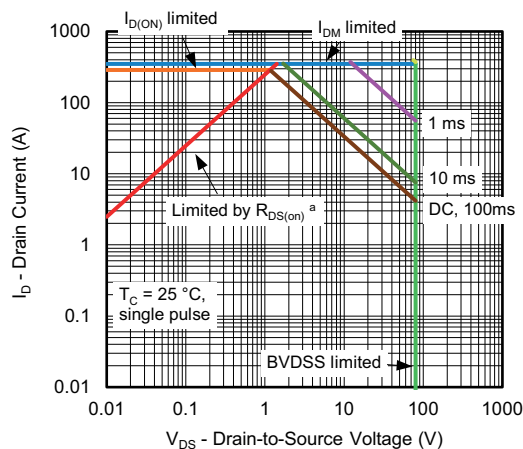
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient



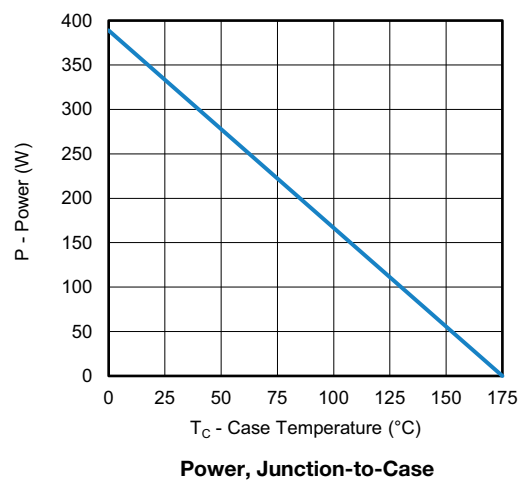
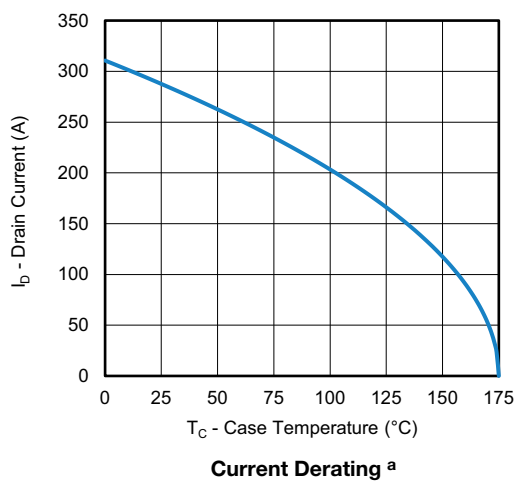
Safe Operating Area, Junction-to-Ambient

Note

a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

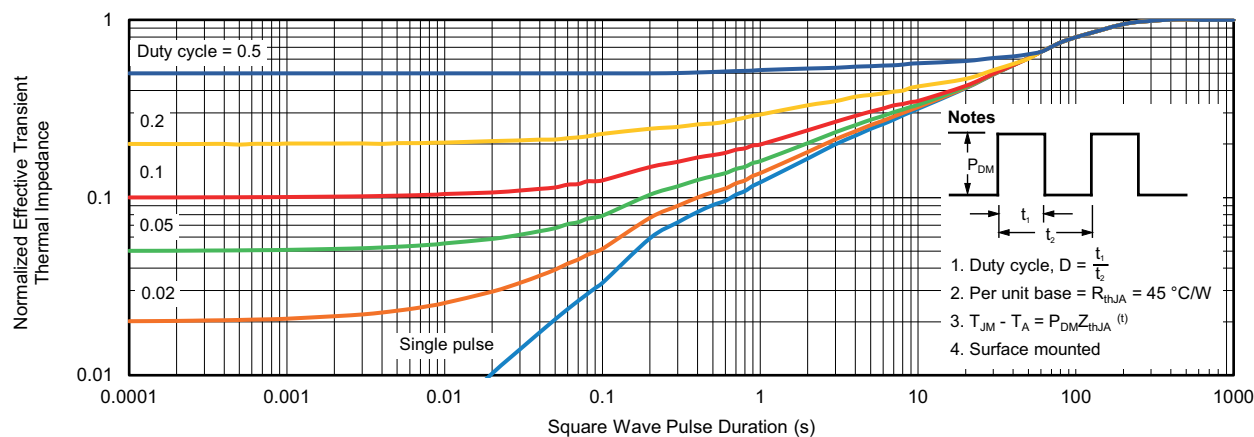


Note

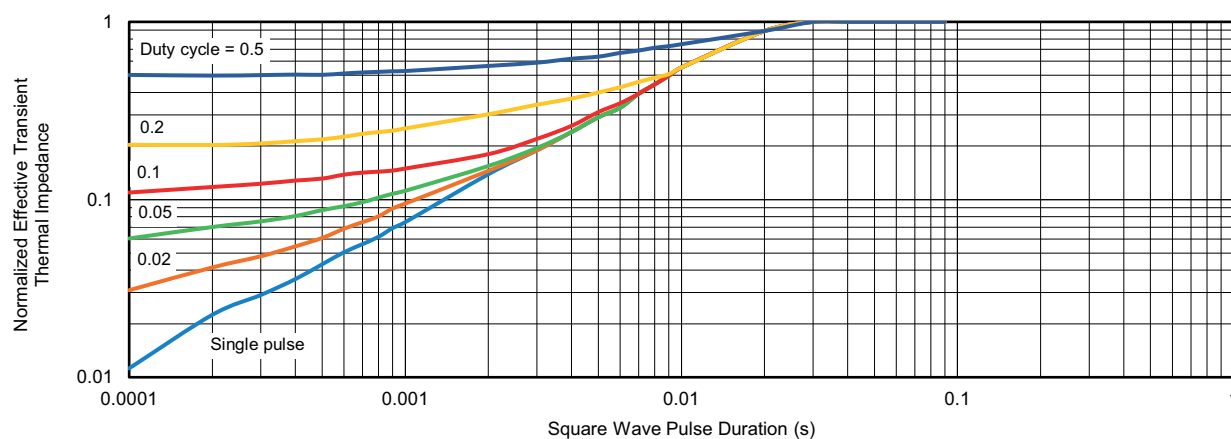
- a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

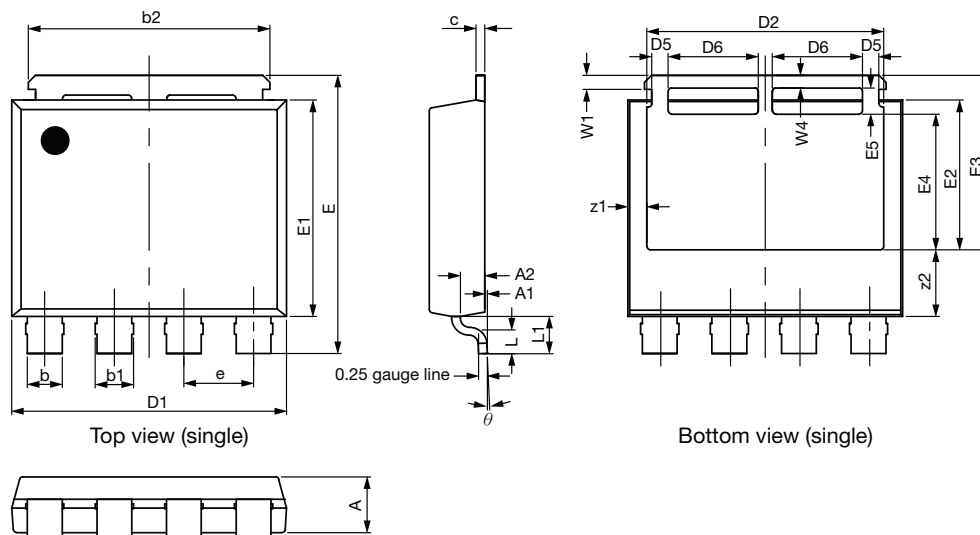


Normalized Thermal Transient Impedance, Junction-to-Case

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PowerPAK® 8 x 8L BWL Case Outline 2



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	1.50	1.60	1.70	0.059	0.063	0.067
A1	0.00	-	0.127	0.000	-	0.005
A2	0.655	0.705	0.755	0.026	0.028	0.030
b	0.92	1.00	1.08	0.036	0.039	0.043
b1	1.02	1.10	1.18	0.040	0.043	0.046
b2	6.84	6.94	7.04	0.269	0.273	0.277
c	0.20	0.25	0.30	0.008	0.010	0.012
D1	7.80	7.90	8.00	0.307	0.311	0.315
D2	6.70	6.80	6.90	0.264	0.268	0.272
D5	0.37	0.47	0.57	0.015	0.019	0.022
D6	2.49	2.59	2.69	0.098	0.102	0.106
e	1.97	2.00	2.03	0.078	0.079	0.080
E	7.90	8.00	8.10	0.311	0.315	0.319
E1	6.12	6.22	6.32	0.241	0.245	0.249
E2	4.21	4.31	4.41	0.166	0.170	0.174
E3	4.92	5.02	5.12	0.194	0.198	0.202
E4	3.80	3.90	4.00	0.150	0.154	0.157
E5	0.65	0.75	0.85	0.026	0.030	0.033
L	0.61	0.68	0.75	0.024	0.027	0.030
L1	1.00	1.07	1.15	0.039	0.042	0.045
W1	0.30	0.40	0.50	0.012	0.016	0.020
W4	0.32	0.37	0.42	0.013	0.015	0.017
z1	0.45	0.55	0.65	0.018	0.022	0.026
z2	1.81	1.91	2.01	0.071	0.075	0.079
θ	0°	-	5°	0°	-	5°
ECN: S19-0643-Rev. B, 05-Aug-2019 DWG: 6073						

Note

- Millimeter will govern



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